



# BT136S-800F

4Q Triac

30 September 2013

Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional and phase control applications.

## 2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

## 4. Quick reference data

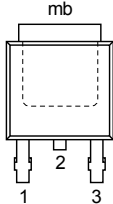

Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ;<br>$t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 25  | A    |
| $I_{T(\text{RMS})}$           | RMS on-state current                 | full sine wave; $T_{mb} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ;<br><a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | -   | 4   | A    |
| <b>Static characteristics</b> |                                      |   |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                           | -   | 5   | 25  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                           | -   | 8   | 25  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                           | -   | 11  | 25  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                           | -   | 30  | 70  | mA   |



## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline  | Graphic symbol  |
|-----|--------|--------------------------------|---|---|
| 1   | T1     | main terminal 1                |  <p style="text-align: center;"><b>DPAK (SOT428)</b></p> |  |
| 2   | T2     | main terminal 2                |   |   |
| 3   | G      | gate                           |   |   |
| mb  | T2     | mounting base; main terminal 2 |   |   |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| BT136S-800F | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max | Unit                   |
|---------------------|--------------------------------------|---|-----|-----|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |   | -   | 800 | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>         | -   | 4   | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 25  | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$ ; $t_{\text{p}} = 16.7\text{ ms}$   | -   | 27  | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN   | -   | 3.1 | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+                  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-                  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-                  | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+                  | -   | 10  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |   | -   | 2   | A                      |
| $P_{\text{GM}}$     | peak gate power                      |   | -   | 5   | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period   | -   | 0.5 | W                      |
| $T_{\text{stg}}$    | storage temperature                  |   | -40 | 150 | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |   | -   | 125 | $^{\circ}\text{C}$     |

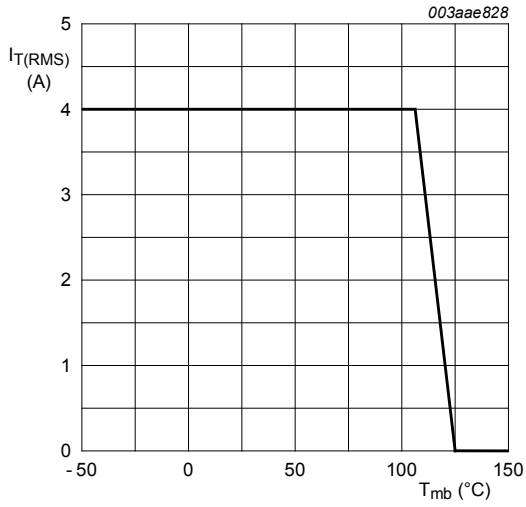
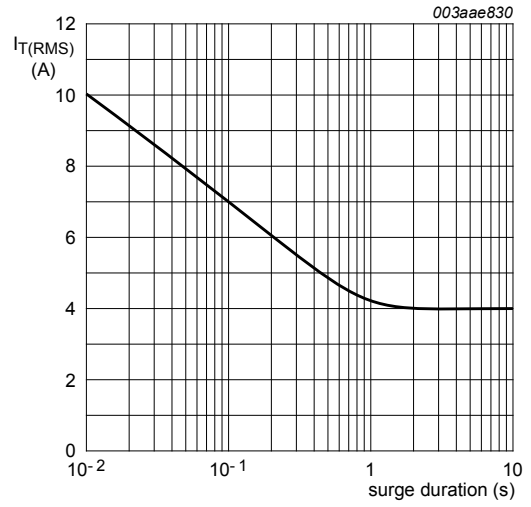
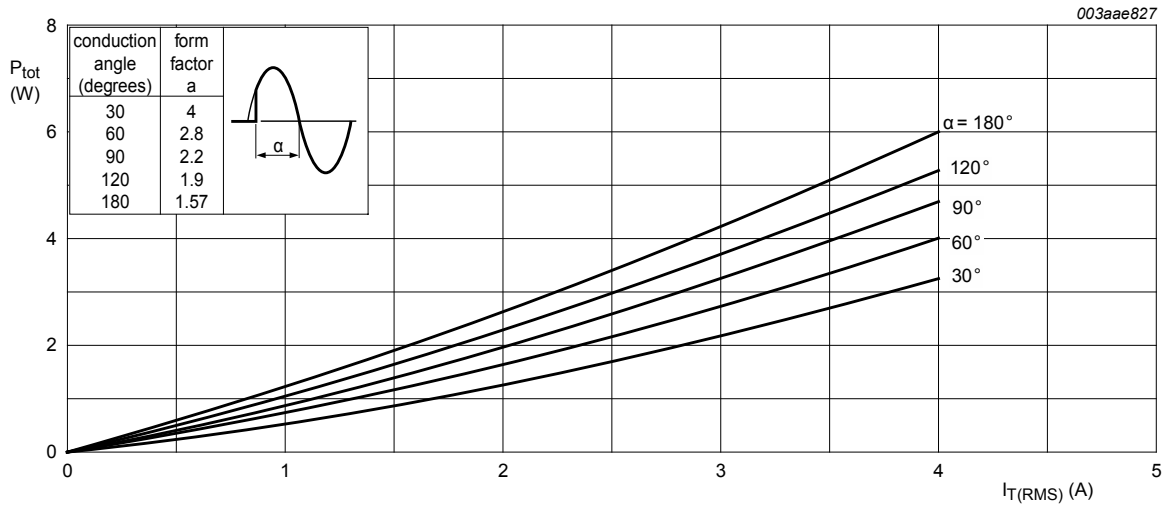


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



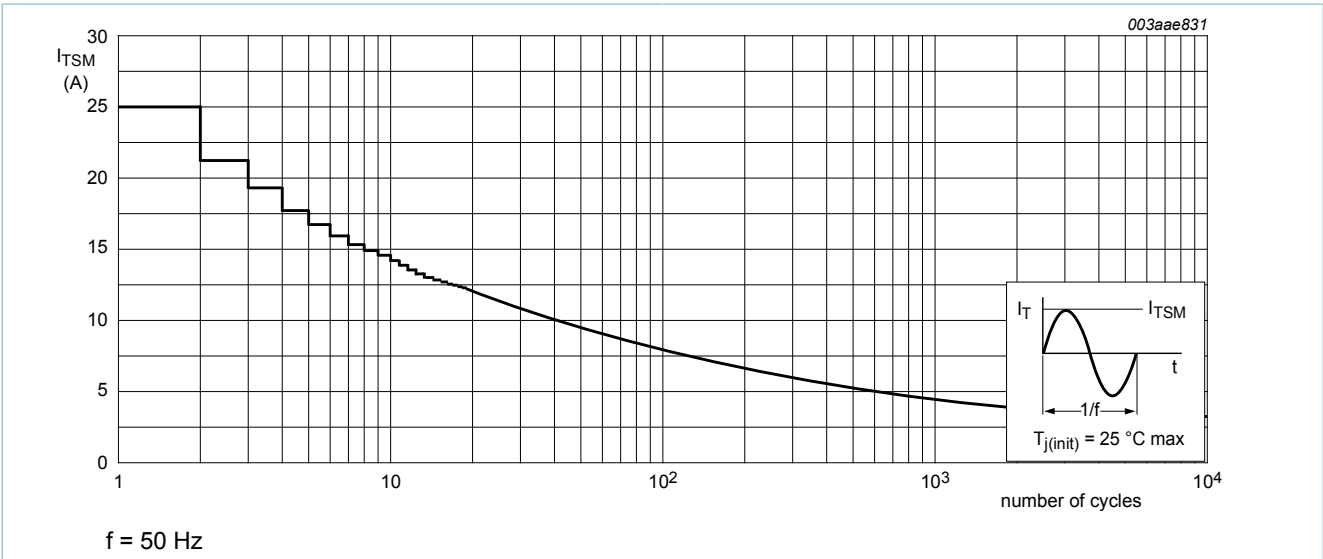
f = 50 Hz  
 $T_{mb} \leq 107\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

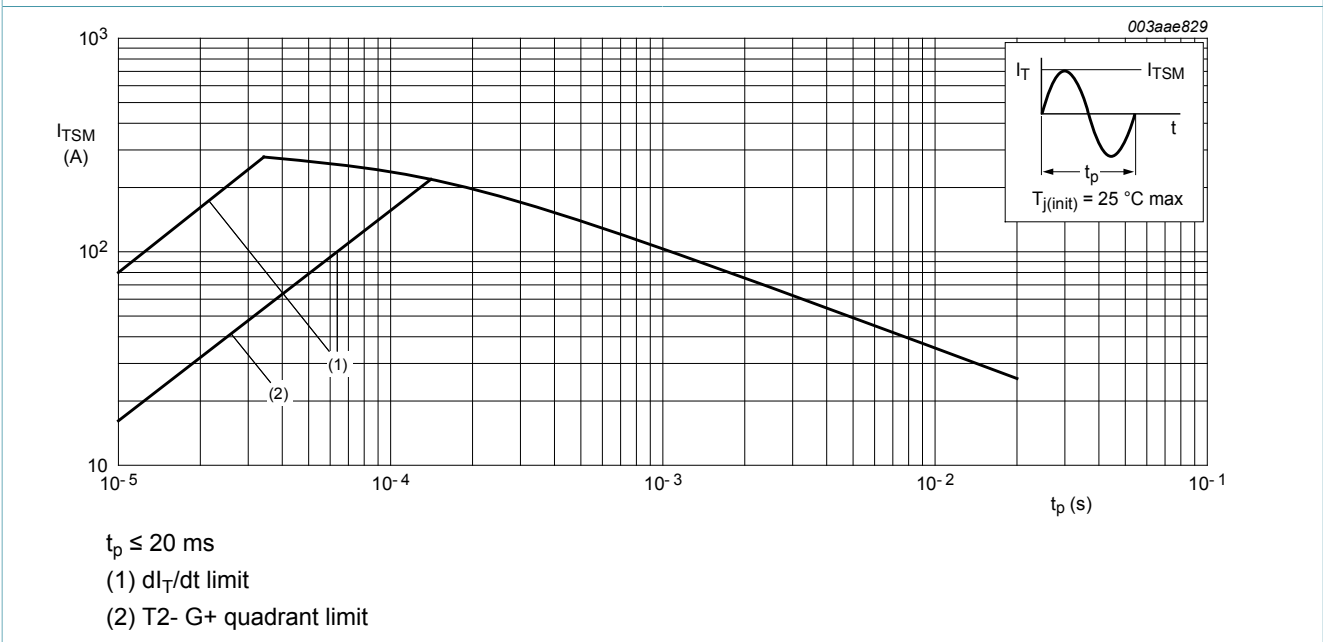


$\alpha$  = conduction angle  
 a = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions  | Min | Typ | Max | Unit |
|----------------|---|---|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | half cycle; <a href="#">Fig. 6</a>  | -   | -   | 3.7 | K/W  |
|                |   | full cycle; <a href="#">Fig. 6</a>  | -   | -   | 3   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air; printed circuit board (FR4) mounted; standard footprint, single-sided copper, tin-plated | -   | 75  | -   | K/W  |

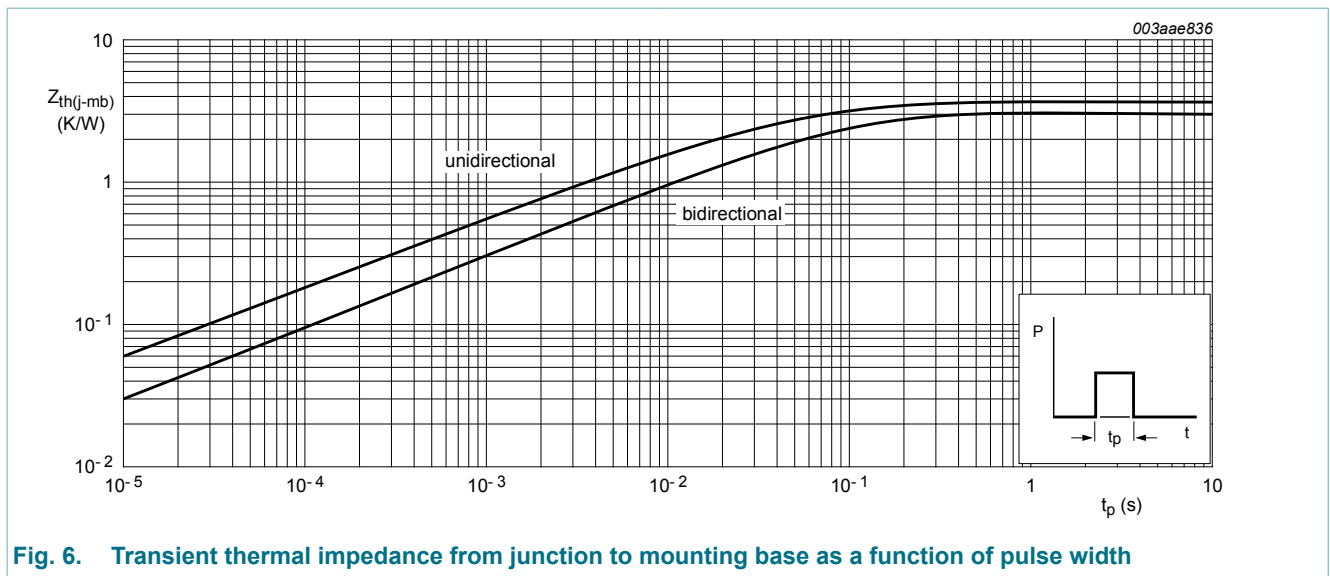
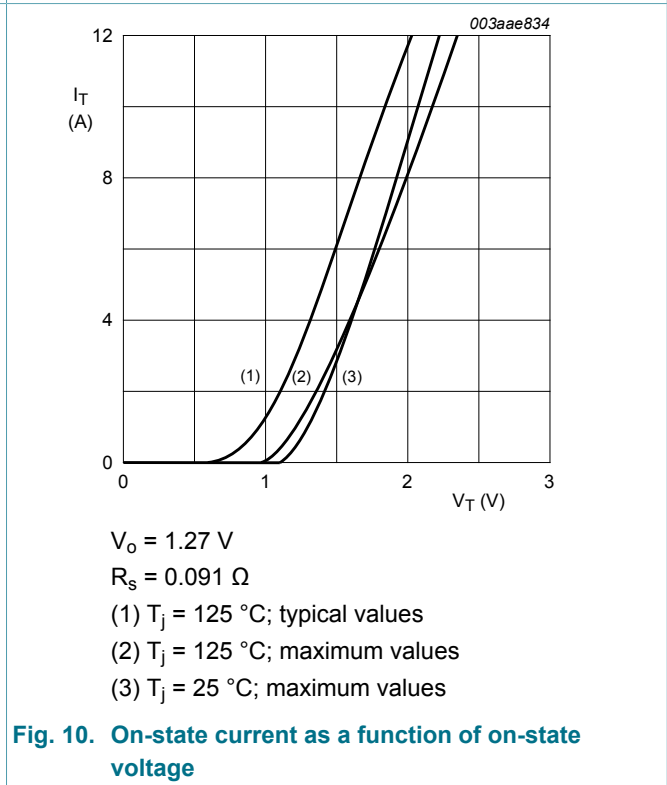
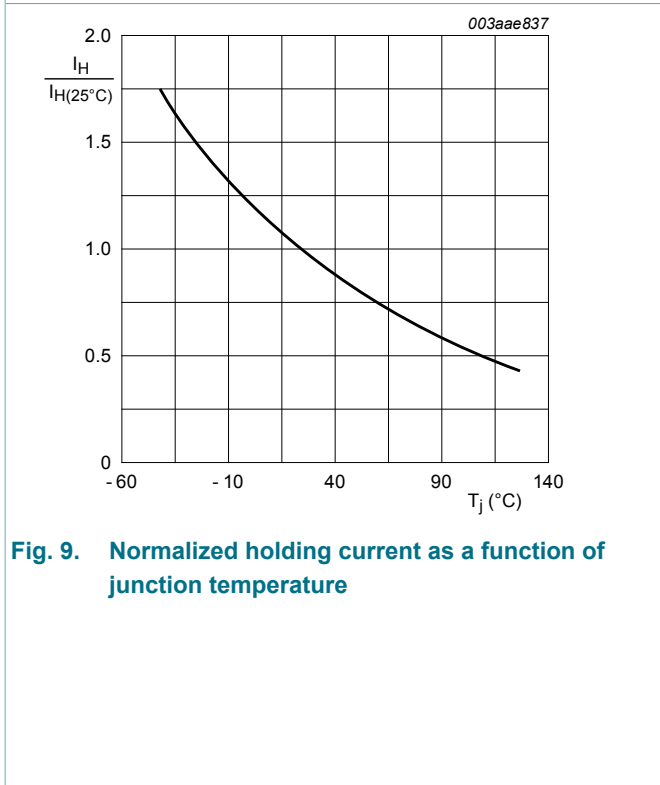
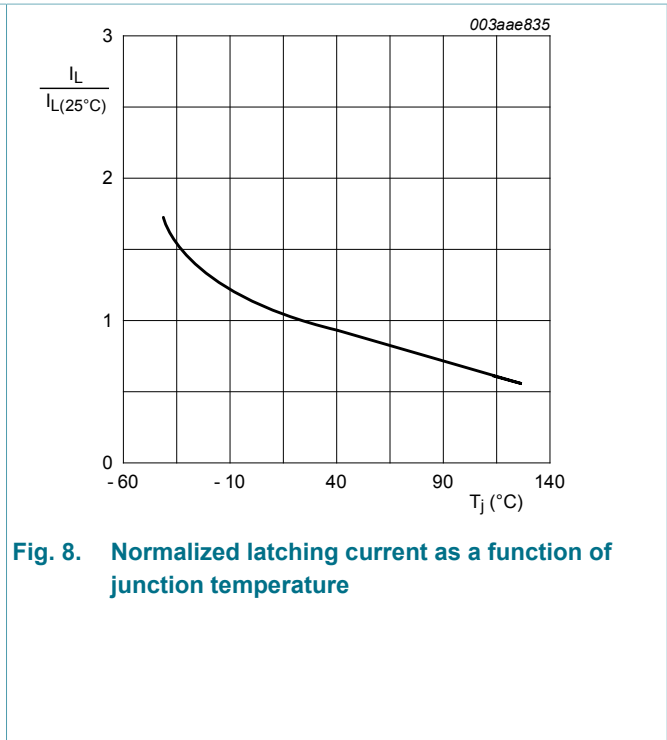
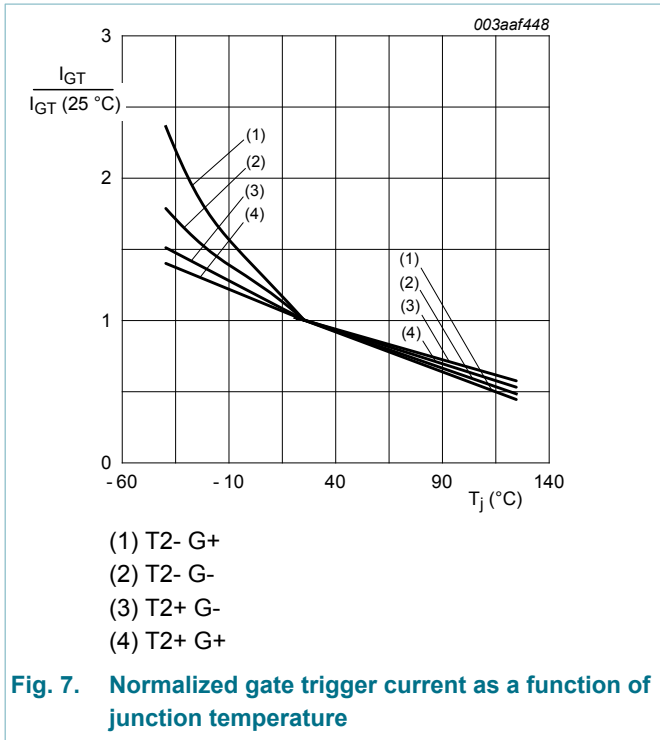


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions  | Min  | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|---|------|-----|-----|------------|
| <b>Static characteristics</b>  |                                       |   |      |     |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                       | -    | 5   | 25  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                       | -    | 8   | 25  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                       | -    | 11  | 25  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                       | -    | 30  | 70  | mA         |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                       | -    | 7   | 20  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                       | -    | 16  | 30  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                       | -    | 5   | 20  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>                       | -    | 7   | 30  | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>   | -    | 5   | 15  | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -    | 1.4 | 1.7 | V          |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 11</a>                              | -    | 0.7 | 1   | V          |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$ ;<br><a href="#">Fig. 11</a>                            | 0.25 | 0.4 | -   | V          |
| $I_D$                          | off-state current                     | $V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$  | -    | 0.1 | 0.5 | mA         |
| <b>Dynamic characteristics</b> |                                       |   |      |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 50   | 250 | -   | V/ $\mu$ s |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 95\text{ °C}$ ; $dI_{com}/dt = 1.8\text{ A/ms}$ ; $I_T = 4\text{ A}$ ; gate open circuit      | -    | 50  | -   | V/ $\mu$ s |
| $t_{gt}$                       | gate-controlled turn-on time          | $I_{TM} = 6\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ mA}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$                   | -    | 2   | -   | $\mu$ s    |



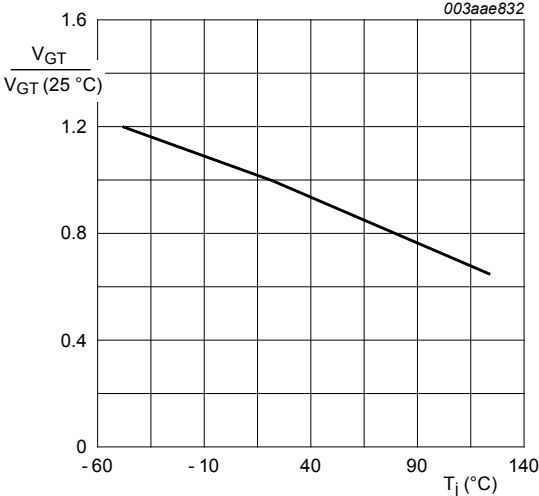
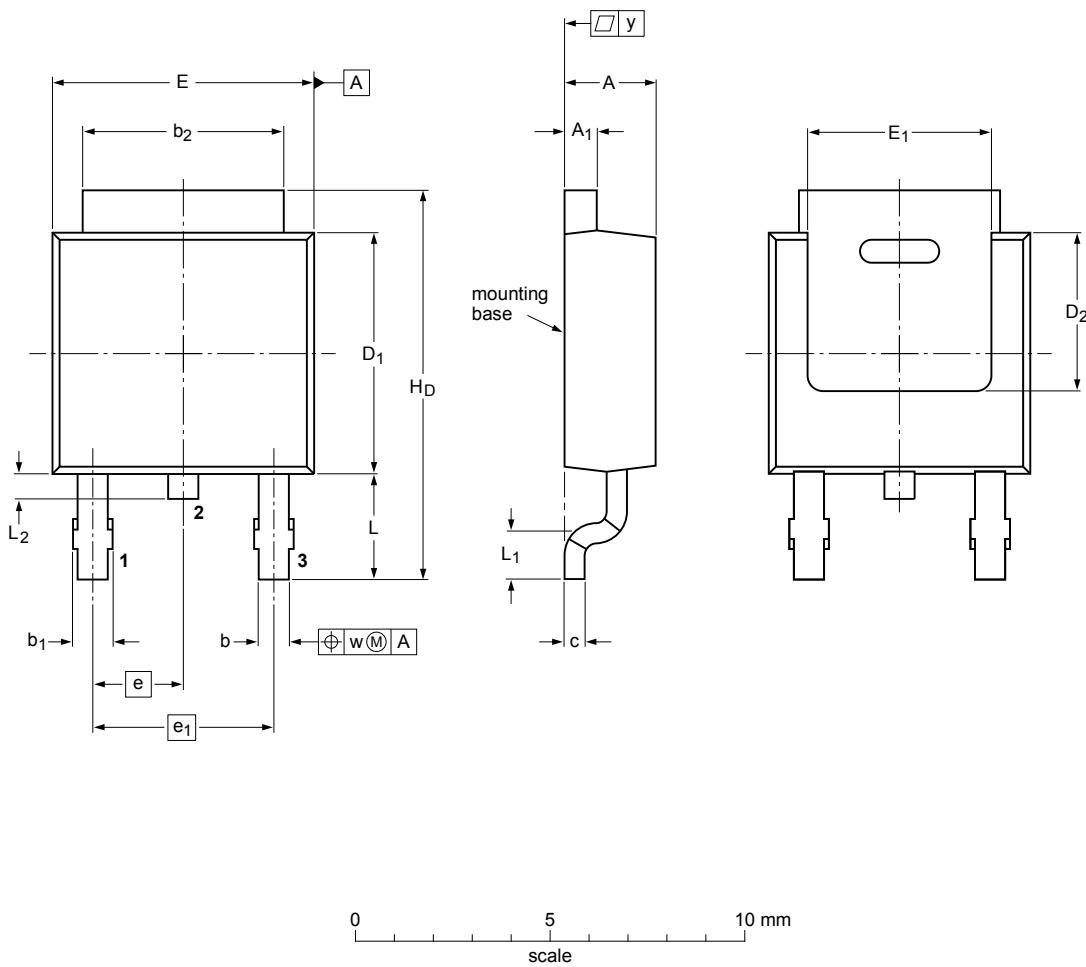


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

### 10. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) SOT428



**DIMENSIONS** (mm are the original dimensions)

| UNIT | A            | A <sub>1</sub> | b            | b <sub>1</sub> | b <sub>2</sub> | c            | D <sub>1</sub> | D <sub>2</sub><br>min | E            | E <sub>1</sub><br>min | e     | e <sub>1</sub> | H <sub>D</sub> | L            | L <sub>1</sub><br>min | L <sub>2</sub> | w   | y<br>max |
|------|--------------|----------------|--------------|----------------|----------------|--------------|----------------|-----------------------|--------------|-----------------------|-------|----------------|----------------|--------------|-----------------------|----------------|-----|----------|
| mm   | 2.38<br>2.22 | 0.93<br>0.46   | 0.89<br>0.71 | 1.1<br>0.9     | 5.46<br>5.00   | 0.56<br>0.20 | 6.22<br>5.98   | 4.0                   | 6.73<br>6.47 | 4.45                  | 2.285 | 4.57           | 10.4<br>9.6    | 2.95<br>2.55 | 0.5                   | 0.9<br>0.5     | 0.2 | 0.2      |

| OUTLINE VERSION | REFERENCES |        |       | EUROPEAN PROJECTION | ISSUE DATE           |
|-----------------|------------|--------|-------|---------------------|----------------------|
|                 | IEC        | JEDEC  | JEITA |                     |                      |
| SOT428          |            | TO-252 | SC-63 |                     | 06-02-14<br>06-03-16 |

Fig. 12. Package outline DPAK (SOT428)

## 11. Soldering

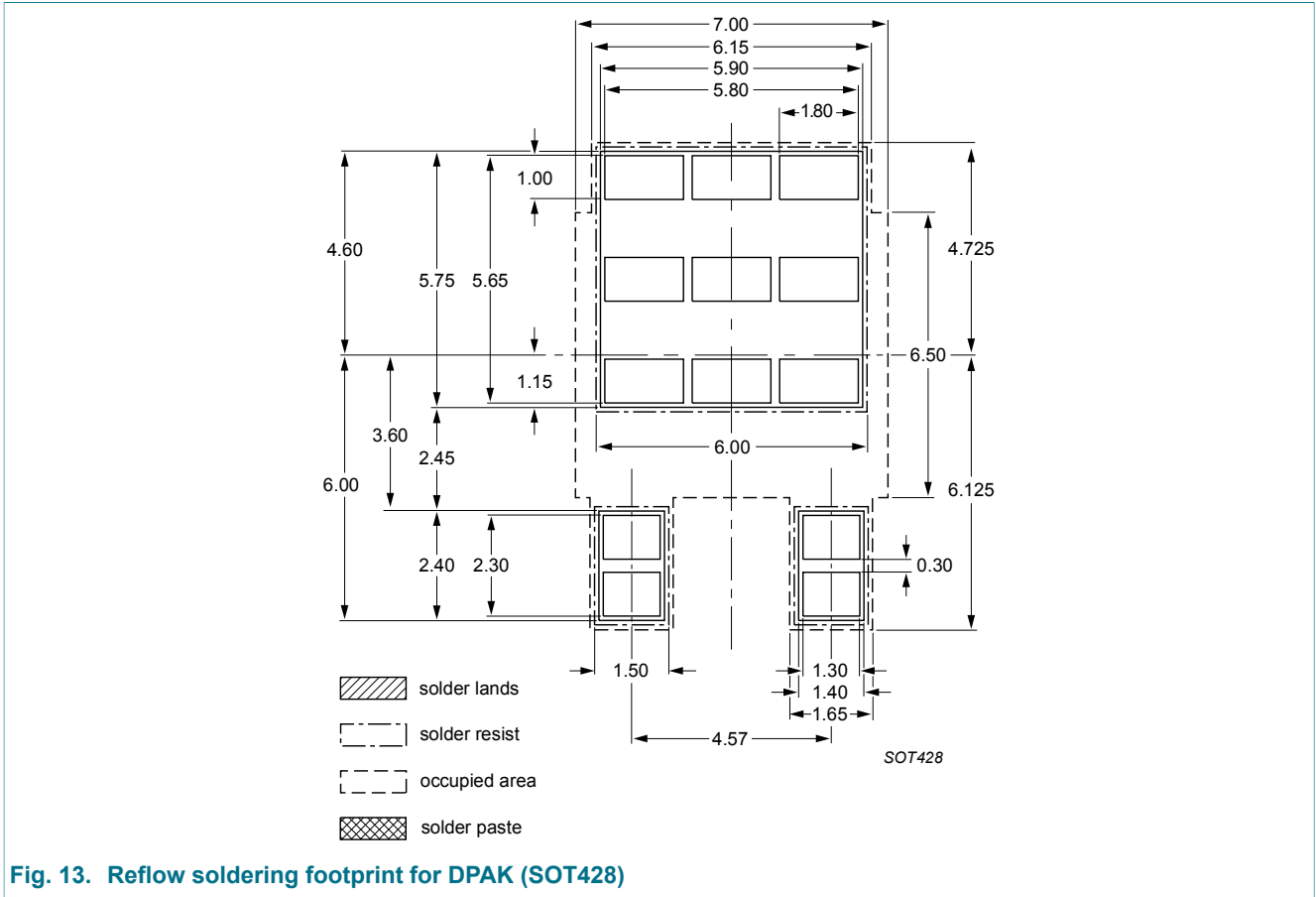


Fig. 13. Reflow soldering footprint for DPAK (SOT428)

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|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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